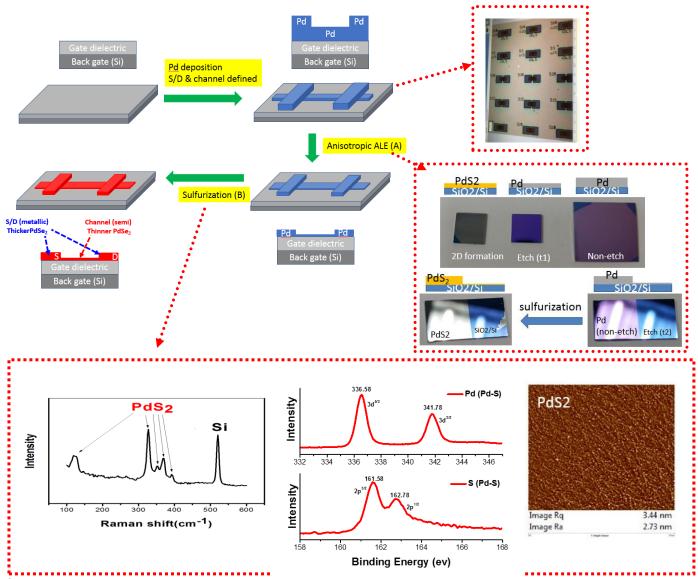
Synthesis of Layered PdS₂ film and Homo-junction Device Fabrication

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